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03500.017757.APPLICATION NO.  
10/535,196

APPLICANT

HIDEYA KUMONI

FILING DATE

May 18, 2005

GROUP

1765

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
GNR	2001/0001745 A1	05/24/01	Im et al.	438	747	
	2003/0096489 A1	05/22/03	Im et al.	438	487	
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	7,029,996 B2	04/18/06	Im et al	438	487	

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	A. Hara et al. "Large Grain Poly-Si TFTs by Scanning CW Laser Crystallization", AM-LCD '02 Digest of Tech. Paper, pp. 227-230 (2002).
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EXAMINER

DATE CONSIDERED

4/19/07

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 1 of 1

FORM PTO 1449 (modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY DOCKET NO. 03500.017757.	APPLICATION NO. 107535196 NOT YET ASSIGNED			
LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)			APPLICANT HIDEYA KUMONI				
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	WO	01/18854 A1	03/15/01	WIPO			Yes
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GMR		Fortunato G., et al. "Excimer Laser Crystallization Techniques for Polysilicon TFTs", Applied Surface Science, vol. 154-155, pp. 95-104, February 2000.					
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.